Product data sheet

1. General description

Planar passivated four quadrant triac in a SOT223 surface-mountable plastic package. This very sensitive gate "series D" triac is intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

2. Features and benefits

- Direct interfacing to logic level ICs
- Direct interfacing to low power gate drivers and microcontrollers
- Medium blocking voltage capability
- Planar passivated for voltage ruggedness and reliability
- Surface-mountable package
- Triggering in all four quadrants
- Very sensitive gate

3. Applications

- AC Fan controller
- General purpose low power phase control
- General purpose low power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	400	V
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 20 \text{ms}$; Fig. 4; Fig. 5	-	-	9	A
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 107$ °C; $\underline{Fig. 1}$; $\underline{Fig. 2}$; $\underline{Fig. 3}$	-	-	0.8	А
Static charact	teristics					
I _{GT}	gate trigger current	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ \text{ G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$	-	1	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	2	5	mA





NXP Semiconductors BT1308W-400D

4Q Triac

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } Fig. 9$	-	2	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$	-	4	7	mA

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2—T1
2	T2	main terminal 2		G sym051
3	G	gate		3
4	T2	main terminal 2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT1308W-400D	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223			

Product data sheet

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	400	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 107 ^{\circ}\text{C}$; Fig. 1; Fig. 2; Fig. 3	-	0.8	A
I _{TSM}	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	9	A
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	10	A
I ² t	I2t for fusing	t _p = 10 ms; SIN	-	0.32	A ² s
dl _T /dt	rate of rise of on-state current	I_T = 1 A; I_G = 20 mA; dI_G/dt = 0.2 A/ μ s; T2+ G+	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; $T2+ G-$	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G-	-	50	A/µs
		$I_T = 1 \text{ A}$; $I_G = 20 \text{ mA}$; $dI_G/dt = 0.2 \text{ A/}\mu\text{s}$; T2- G+	-	10	A/µs
I _{GM}	peak gate current		-	1	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20 ms period	-	0.1	W
T _{stg}	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

NXP Semiconductors BT1308W-400D

4Q Triac

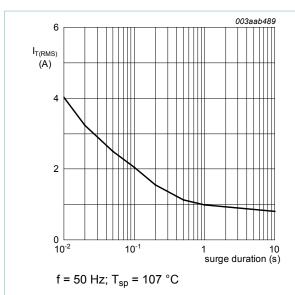


Fig. 1. RMS on-state current as a function of surge duration; maximum values

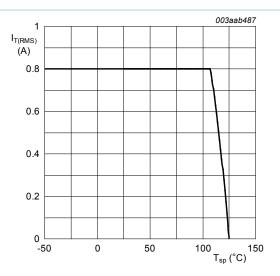
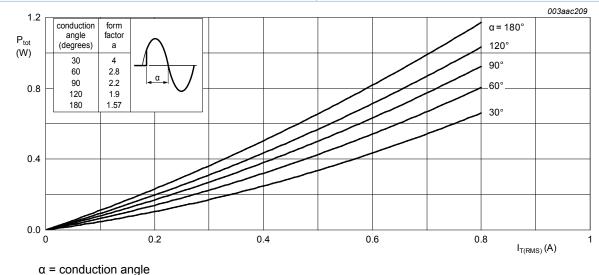


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values



u – conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

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4Q Triac

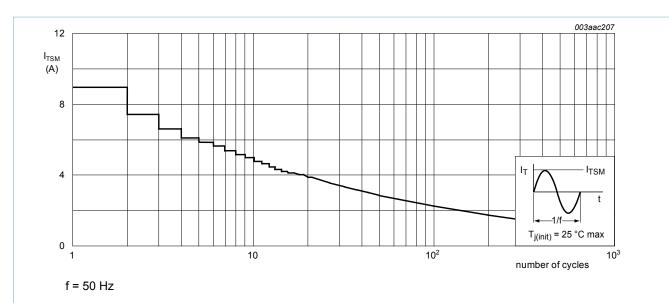
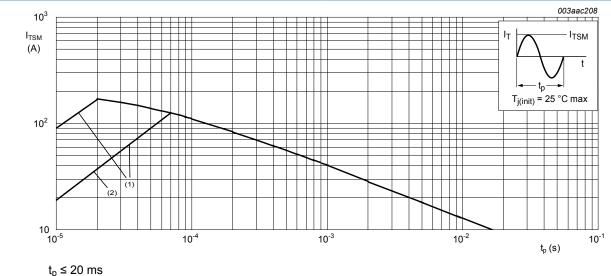


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum



(1) dI_T/dt limit

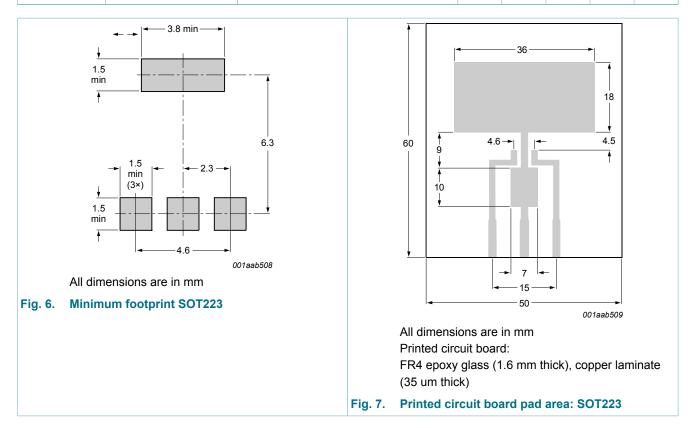
(2) T2- G+ quadrant limit

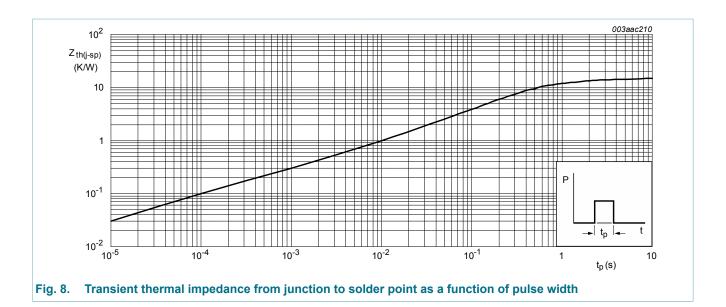
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle; Fig. 8	-	-	15	K/W
R _{th(j-a)}	thermal resistance	full cycle; for minimum footprint; Fig. 6	-	156	-	K/W
	from junction to ambient	full cycle; for pad area; Fig. 7	-	70	-	K/W



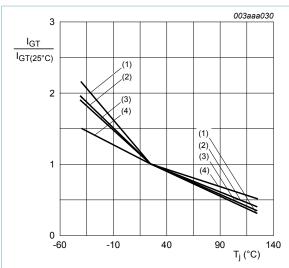


9. Characteristics

Table 6 Characteristics

Table 6. Symbol	Characteristics Parameter	Conditions	Min	Тур	Max	Unit
	aracteristics			7.		
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	1	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ \text{ G-};$ $T_j = 25 ^{\circ}\text{C}; Fig. 9$	-	2	5	mA
		$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- \text{ G-};$ $T_j = 25 \text{ °C}; Fig. 9$	-	2	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G+; T _j = 25 °C; <u>Fig. 9</u>	-	4	7	mA
lL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 10</u>	-	5	10	mA
		V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 10</u>	-	1	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 10}$	-	1	10	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G+};$ $T_j = 25 ^{\circ}\text{C}; \underline{\text{Fig. 10}}$	-	2	10	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	1	10	mA
V _T	on-state voltage	I _T = 0.85 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.35	1.6	V
V_{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.9	1.5	V
		$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 \text{ °C};$ Fig. 13	0.1	0.7	-	V
I _D	off-state current	V _D = 400 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic	characteristics		1			,
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 268 V; T_j = 110 °C; (V_{DM} = 67% of V_{DRM}); exponential waveform; gate open circuit	30	45	-	V/µs
dV _{com} /dt	rate of change of commutating voltage	$V_D = 400 \text{ V; } T_j = 50 \text{ °C; } dI_{com}/dt = 0.3 \text{ A/}$ ms; $I_T = 0.84 \text{ A; } gate open circuit}$	-	5	-	V/µs
t _{gt}	gate-controlled turn-on time	I_{TM} = 1 A; V_D = 400 V; I_G = 25 mA; $dI_G/$ dt = 5 A/ μ s	-	2	-	μs

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- (1) T2+ G+
- (2) T2- G+
- (3) T2- G-
- (4) T2+ G-

Fig. 9. Normalized gate trigger current as a function of junction temperature

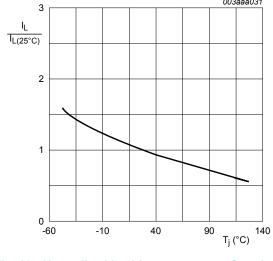


Fig. 10. Normalized latching current as a function of junction temperature

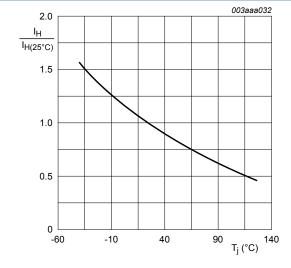
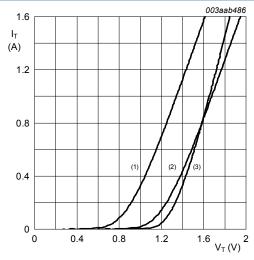


Fig. 11. Normalized holding current as a function of junction temperature



 $V_o = 1.171 \text{ V}; R_s = 0.5125 \Omega$

- (1) T_i = 125 °C; typical values
- (2) T_i = 125 °C; maximum values
- (3) T_i = 25 °C; maximum values

Fig. 12. On-state current as a function of on-state voltage

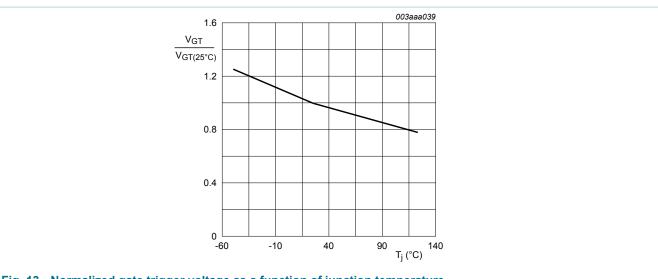
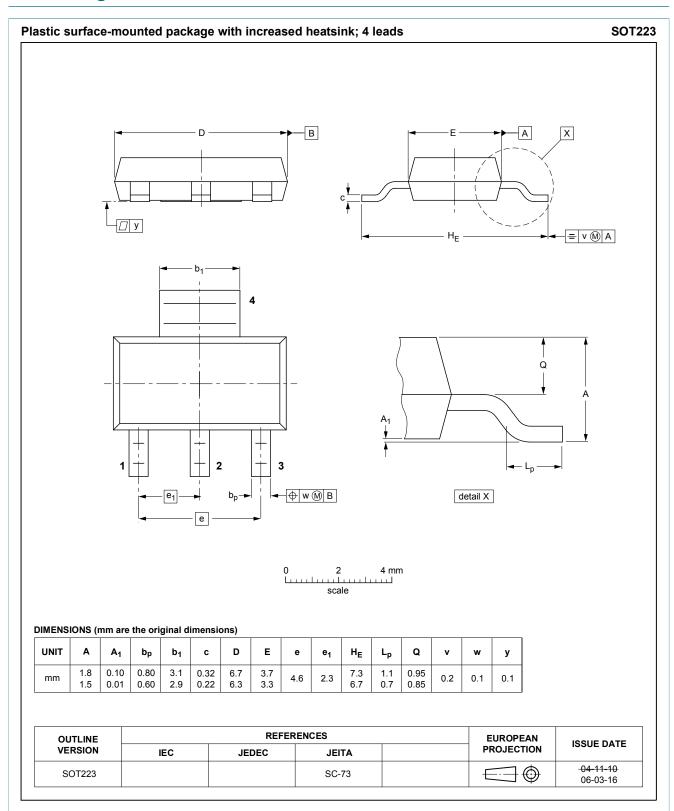
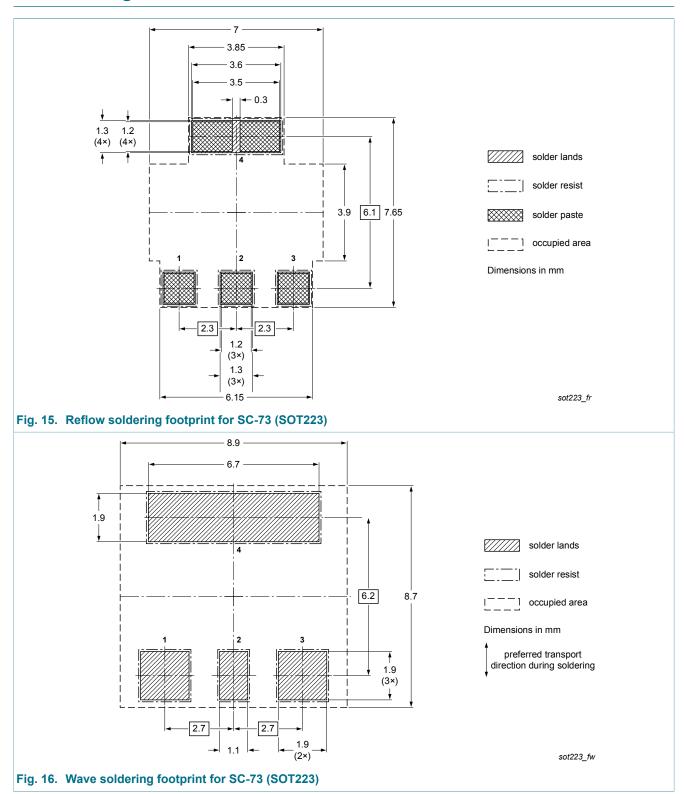


Fig. 13. Normalized gate trigger voltage as a function of junction temperature

10. Package outline



11. Soldering



12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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